

BZX85C3V3RL Series

1 Watt DO-41 Hermetically Sealed Glass Zener Voltage Regulators

This is a complete series of 1 Watt Zener diodes with limits and excellent operating characteristics that reflect the superior capabilities of silicon-oxide passivated junctions. All this in an axial-lead hermetically sealed glass package that offers protection in all common environmental conditions.

Specification Features:

- Zener Voltage Range – 3.3 V to 85 V
- ESD Rating of Class 3 (>16 KV) per Human Body Model
- DO-41 (DO-204AL) Package
- Double Slug Type Construction
- Metallurgical Bonded Construction
- Oxide Passivated Die

Mechanical Characteristics:

CASE: Double slug type, hermetically sealed glass

FINISH: All external surfaces are corrosion resistant and leads are readily solderable

MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 230°C, 1/16" from the case for 10 seconds

POLARITY: Cathode indicated by polarity band

MOUNTING POSITION: Any

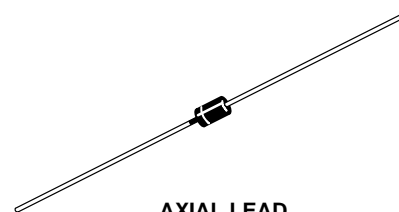
MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|----------------|----------------|------------|
| Max. Steady State Power Dissipation @ $T_L \leq 50^\circ\text{C}$, Lead Length = 3/8" Derate above 50°C | P_D | 1 6.67 | W mW/°C |
| Operating and Storage Temperature Range | T_J, T_{stg} | -65 to +200 | °C |



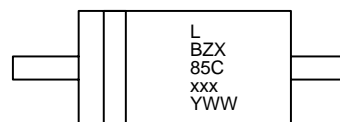
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AXIAL LEAD
CASE 59
GLASS

MARKING DIAGRAM



L = Assembly Location
BZX85Cxxx = Device Code
(See Table Next Page)
Y = Year
WW = Work Week

ORDERING INFORMATION

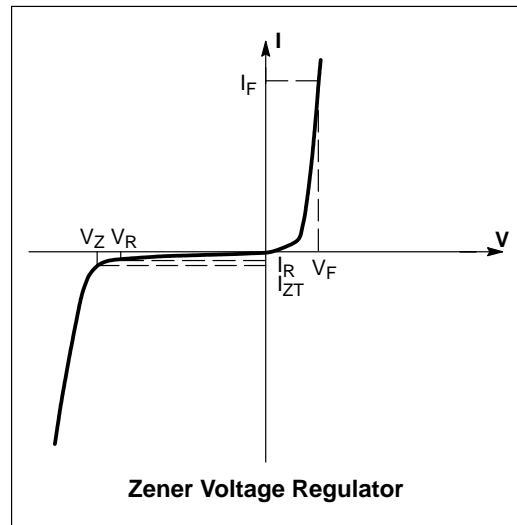
| Device | Package | Shipping |
|--------------|------------|------------------|
| BZX85CxxxRL | Axial Lead | 6000/Tape & Reel |
| BZX85CxxxRL2 | Axial Lead | 6000/Tape & Reel |

* The "2" suffix refers to 26 mm tape spacing.

BZX85C3V3RL Series

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted, $V_F = 1.2\text{ V Max.}$, $I_F = 200\text{ mA}$ for all types)

| Symbol | Parameter |
|----------|--|
| V_Z | Reverse Zener Voltage @ I_{ZT} |
| I_{ZT} | Reverse Current |
| Z_{ZT} | Maximum Zener Impedance @ I_{ZT} |
| I_{ZK} | Reverse Current |
| Z_{ZK} | Maximum Zener Impedance @ I_{ZK} |
| I_R | Reverse Leakage Current @ V_R |
| V_R | Breakdown Voltage |
| I_F | Forward Current |
| V_F | Forward Voltage @ I_F |
| I_R | Surge Current @ $T_A = 25^\circ\text{C}$ |



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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted, $V_F = 1.2\text{ V Max.}$, $I_F = 200\text{ mA}$ for all types)

| Device (Note 1) | Device Marking | Zener Voltage (Notes 2 and 3) | | | | Zener Impedance (Note 4) | | | Leakage Current | | I_R (Note 5) |
|--------------------|-------------------|-------------------------------|-------|------|------------|--------------------------|---------------------|------|-------------------|-------|-------------------|
| | | V_Z (Volts) | | | @ I_{ZT} | Z_{ZT} @ I_{ZT} | Z_{ZK} @ I_{ZK} | | I_R @ V_R | | |
| | | Min | Nom | Max | mA | Ω | Ω | mA | $\mu\text{A Max}$ | Volts | mA |
| BZX85C3V3RL | BZX85C3V3 | 3.1 | 3.3 | 3.5 | 80 | 20 | 400 | 1 | 1 | 60 | 1380 |
| BZX85C3V6RL | BZX85C3V6 | 3.4 | 3.6 | 3.8 | 60 | 15 | 500 | 1 | 1 | 30 | 1260 |
| BZX85C3V9RL | BZX85C3V9 | 3.7 | 3.9 | 4.1 | 60 | 15 | 500 | 1 | 1 | 5 | 1190 |
| BZX85C4V3RL | BZX85C4V3 | 4.0 | 4.3 | 4.6 | 50 | 13 | 500 | 1 | 1 | 3 | 1070 |
| BZX85C4V7RL | BZX85C4V7 | 4.4 | 4.7 | 5.0 | 45 | 13 | 600 | 1 | 1.5 | 3 | 970 |
| BZX85C5V1RL | BZX85C5V1 | 4.8 | 5.1 | 5.4 | 45 | 10 | 500 | 1 | 2 | 1 | 890 |
| BZX85C5V6RL | BZX85C5V6 | 5.2 | 5.6 | 6.0 | 45 | 7 | 400 | 1 | 2 | 1 | 810 |
| BZX85C6V2RL | BZX85C6V2 | 5.8 | 6.2 | 6.6 | 35 | 4 | 300 | 1 | 3 | 1 | 730 |
| BZX85C6V8RL | BZX85C6V8 | 6.4 | 6.8 | 7.2 | 35 | 3.5 | 300 | 1 | 4 | 1 | 660 |
| BZX85C7V5RL | BZX85C7V5 | 7.0 | 7.45 | 7.9 | 35 | 3 | 200 | 0.5 | 4.5 | 1 | 605 |
| BZX85C8V2RL | BZX85C8V2 | 7.7 | 8.2 | 8.7 | 25 | 5 | 200 | 0.5 | 5 | 1 | 550 |
| BZX85C9V1RL | BZX85C9V1 | 8.5 | 9.05 | 9.6 | 25 | 5 | 200 | 0.5 | 6.5 | 1 | 500 |
| BZX85C10RL | BZX85C10 | 9.4 | 10 | 10.6 | 25 | 7 | 200 | 0.5 | 7 | 0.5 | 454 |
| BZX85C12RL | BZX85C12 | 11.4 | 12.05 | 12.7 | 20 | 9 | 350 | 0.5 | 8.4 | 0.5 | 380 |
| BZX85C13RL | BZX85C13 | 12.4 | 13.25 | 14.1 | 20 | 10 | 400 | 0.5 | 9.1 | 0.5 | 344 |
| BZX85C15RL | BZX85C15 | 13.8 | 14.7 | 15.6 | 15 | 15 | 500 | 0.5 | 10.5 | 0.5 | 304 |
| BZX85C16RL | BZX85C16 | 15.3 | 16.2 | 17.1 | 15 | 15 | 500 | 0.5 | 11 | 0.5 | 285 |
| BZX85C18RL | BZX85C18 | 16.8 | 17.95 | 19.1 | 15 | 20 | 500 | 0.5 | 12.5 | 0.5 | 250 |
| BZX85C22RL | BZX85C22 | 20.8 | 22.05 | 23.3 | 10 | 25 | 600 | 0.5 | 15.5 | 0.5 | 205 |
| BZX85C24RL | BZX85C24 | 22.8 | 24.2 | 25.6 | 10 | 25 | 600 | 0.5 | 17 | 0.5 | 190 |
| BZX85C27RL | BZX85C27 | 25.1 | 27 | 28.9 | 8 | 30 | 750 | 0.25 | 19 | 0.5 | 170 |
| BZX85C30RL | BZX85C30 | 28 | 30 | 32 | 8 | 30 | 1000 | 0.25 | 21 | 0.5 | 150 |
| BZX85C33RL | BZX85C33 | 31 | 33 | 35 | 8 | 35 | 1000 | 0.25 | 23 | 0.5 | 135 |
| BZX85C36RL | BZX85C36 | 34 | 36 | 38 | 8 | 40 | 1000 | 0.25 | 25 | 0.5 | 125 |
| BZX85C43RL | BZX85C43 | 40 | 43 | 46 | 6 | 50 | 1000 | 0.25 | 30 | 0.5 | 110 |
| BZX85C47RL | BZX85C47 | 44 | 47 | 50 | 4 | 90 | 1500 | 0.25 | 33 | 0.5 | 95 |
| BZX85C62RL | BZX85C62 | 58 | 62 | 66 | 4 | 125 | 2000 | 0.25 | 43 | 0.5 | 70 |
| BZX85C75RL | BZX85C75 | 70 | 75 | 80 | 4 | 150 | 2000 | 0.25 | 51 | 0.5 | 60 |
| BZX85C82RL | BZX85C82 | 77 | 82 | 87 | 2.7 | 200 | 3000 | 0.25 | 56 | 0.5 | 55 |

1. TOLERANCE AND TYPE NUMBER DESIGNATION

The type numbers listed have zener voltage min/max limits as shown and have a standard tolerance on the nominal zener voltage of $\pm 5\%$.

2. AVAILABILITY OF SPECIAL DIODES

For detailed information on price, availability and delivery of nominal zener voltages between the voltages shown and tighter voltage tolerances, contact your nearest ON Semiconductor representative.

3. ZENER VOLTAGE (V_Z) MEASUREMENT

V_Z measured after the test current has been applied to 40 ± 10 msec, while maintaining the lead temperature (T_L) at $30^\circ\text{C} \pm 1^\circ\text{C}$, $3/8''$ from the diode body.

4. ZENER IMPEDANCE (Z_Z) DERIVATION

The zener impedance is derived from 1 kHz cycle AC voltage, which results when an AC current having an rms value equal to 10% of the DC zener current (I_{ZT} or I_{ZK}) is superimposed on I_{ZT} or I_{ZK} .

5. SURGE CURRENT (I_R) NON-REPETITIVE

The rating listed in the electrical characteristics table is maximum peak, non-repetitive, reverse surge current of 1/2 square wave or equivalent sine wave pulse of 1/120 second duration superimposed on the test current, I_{ZT} . However, actual device capability is as described in Figure 5 of the General Data – DO-41 Glass.

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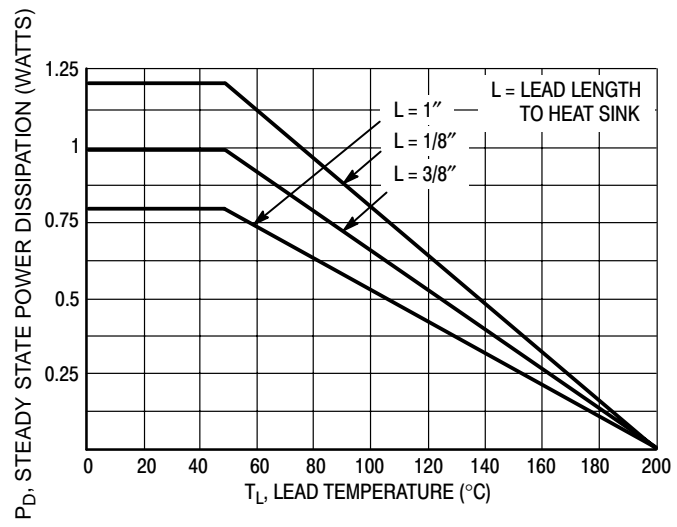
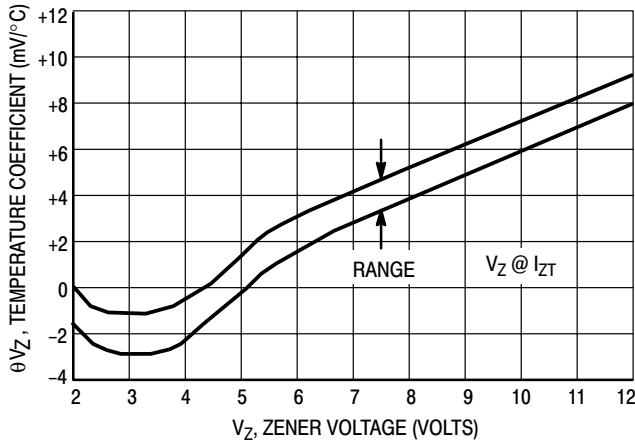


Figure 1. Power Temperature Derating Curve

BZX85C3V3RL Series

a. Range for Units to 12 Volts



b. Range for Units to 12 to 100 Volts

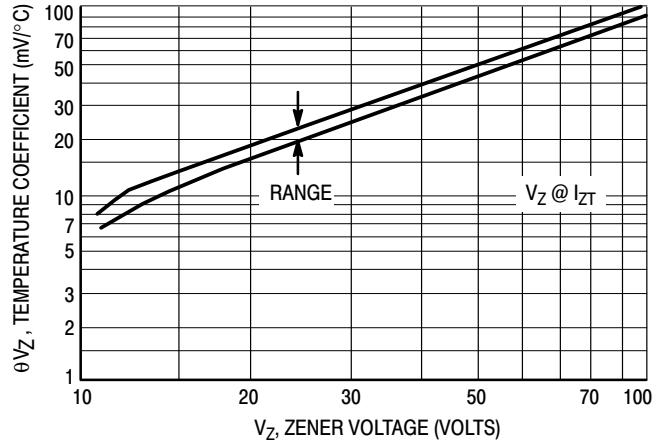


Figure 2. Temperature Coefficients

(-55°C to +150°C temperature range; 90% of the units are in the ranges indicated.)

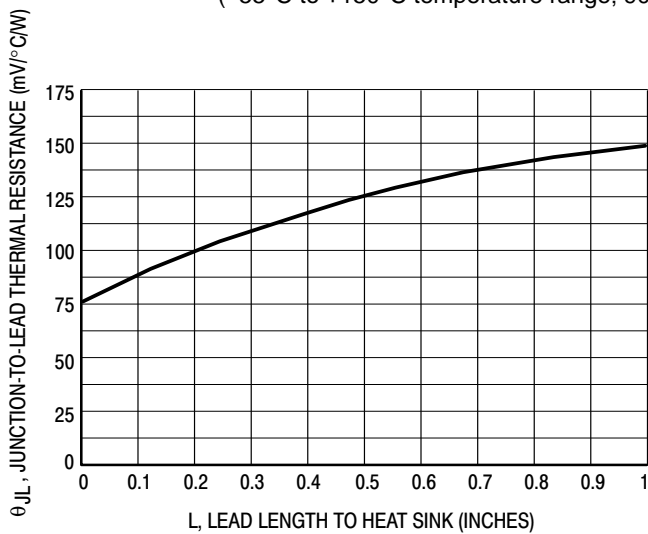


Figure 3. Typical Thermal Resistance versus Lead Length

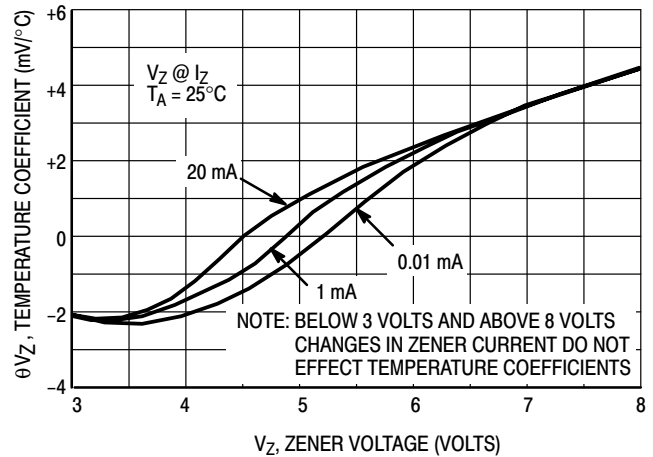
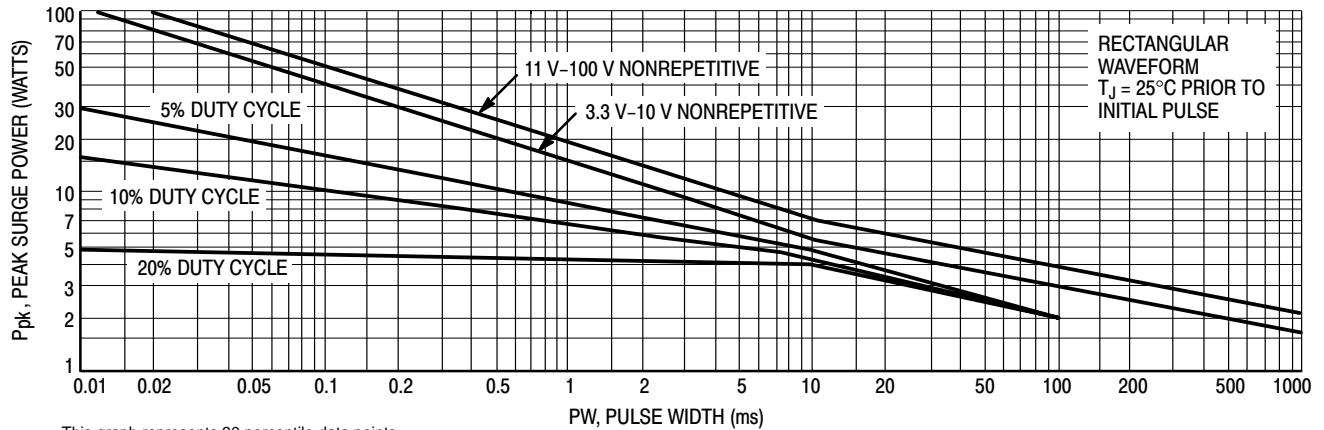


Figure 4. Effect of Zener Current



This graph represents 90 percentile data points.
For worst case design characteristics, multiply surge power by 2/3.

Figure 5. Maximum Surge Power

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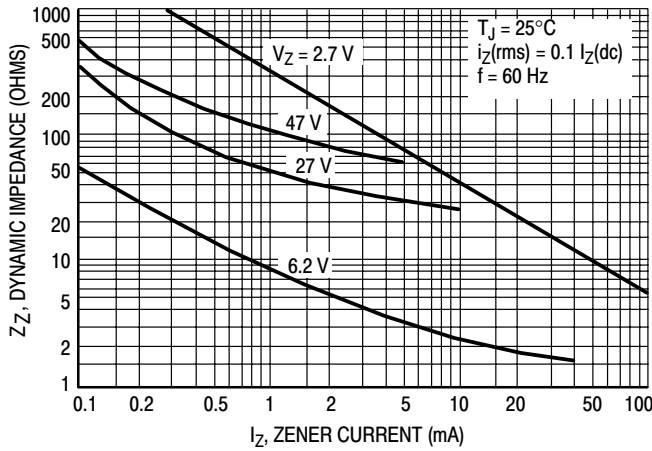


Figure 6. Effect of Zener Current on Zener Impedance

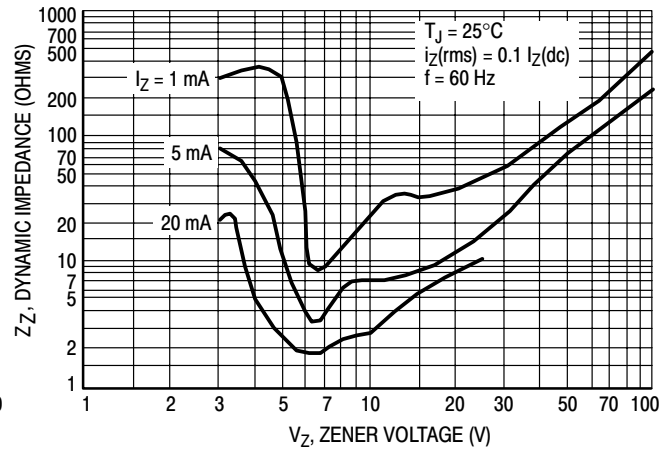


Figure 7. Effect of Zener Voltage on Zener Impedance

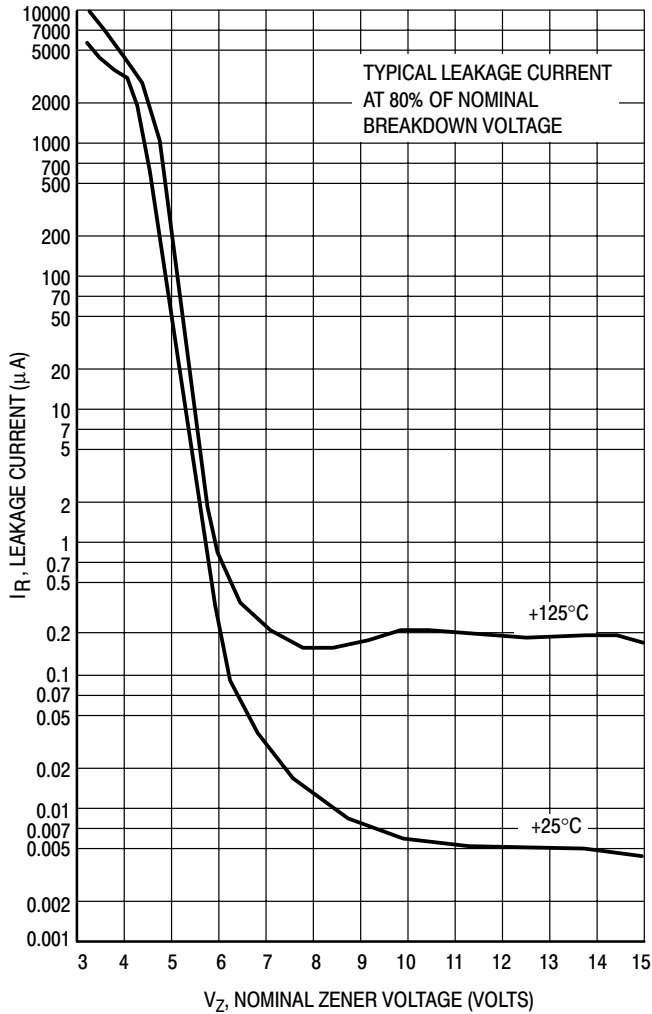


Figure 8. Typical Leakage Current

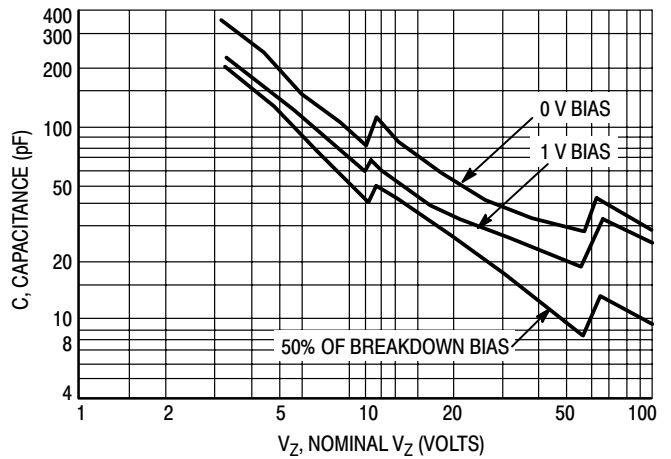


Figure 9. Typical Capacitance versus V_Z

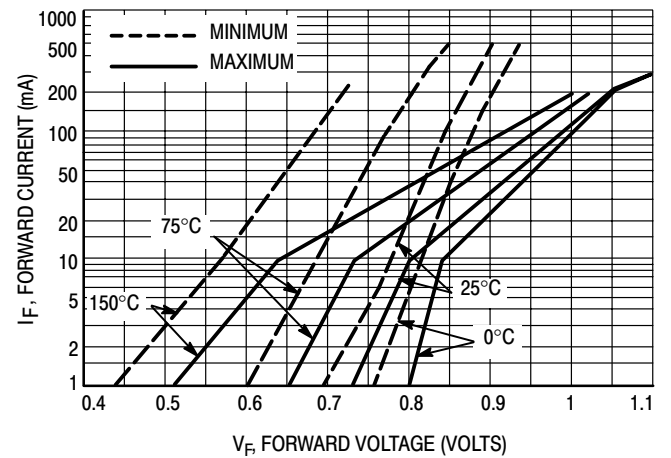


Figure 10. Typical Forward Characteristics

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APPLICATION NOTE

Since the actual voltage available from a given zener diode is temperature dependent, it is necessary to determine junction temperature under any set of operating conditions in order to calculate its value. The following procedure is recommended:

Lead Temperature, T_L , should be determined from:

$$T_L = \theta_{LA} P_D + T_A.$$

θ_{LA} is the lead-to-ambient thermal resistance ($^{\circ}\text{C}/\text{W}$) and P_D is the power dissipation. The value for θ_{LA} will vary and depends on the device mounting method. θ_{LA} is generally 30 to $40^{\circ}\text{C}/\text{W}$ for the various clips and tie points in common use and for printed circuit board wiring.

The temperature of the lead can also be measured using a thermocouple placed on the lead as close as possible to the tie point. The thermal mass connected to the tie point is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_L , the junction temperature may be determined by:

ΔT_{JL} is the increase in junction temperature above the lead temperature and may be found as follows:

$$T_J = T_L + \Delta T_{JL}.$$

$$\Delta T_{JL} = \theta_{JL} P_D.$$

θ_{JL} may be determined from Figure 3 for dc power conditions. For worst-case design, using expected limits of I_Z , limits of P_D and the extremes of $T_J(\Delta T_J)$ may be estimated. Changes in voltage, V_Z , can then be found from:

$$\Delta V = \theta_{VZ} \Delta T_J.$$

θ_{VZ} , the zener voltage temperature coefficient, is found from Figure 2.

Under high power-pulse operation, the zener voltage will vary with time and may also be affected significantly by the zener resistance. For best regulation, keep current excursions as low as possible.

Surge limitations are given in Figure 5. They are lower than would be expected by considering only junction temperature, as current crowding effects cause temperatures to be extremely high in small spots, resulting in device degradation should the limits of Figure 5 be exceeded.

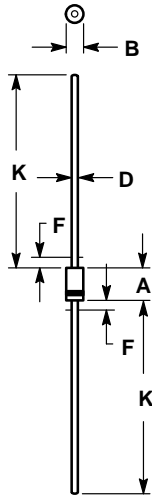
BZX85C3V3RL Series

OUTLINE DIMENSIONS

Zener Voltage Regulators – Axial Leaded

1 Watt DO-41 Glass


GLASS DO-41
CASE 59-10
ISSUE R



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 59-04 OBSOLETE, NEW STANDARD 59-09.
4. 59-03 OBSOLETE, NEW STANDARD 59-10.
5. ALL RULES AND NOTES ASSOCIATED WITH JEDEC DO-41 OUTLINE SHALL APPLY
6. POLARITY DENOTED BY CATHODE BAND.
7. LEAD DIAMETER NOT CONTROLLED WITHIN F DIMENSION.

| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|------|
| | MIN | MAX | MIN | MAX |
| A | 0.161 | 0.205 | 4.10 | 5.20 |
| B | 0.079 | 0.106 | 2.00 | 2.70 |
| D | 0.028 | 0.034 | 0.71 | 0.86 |
| F | --- | 0.050 | --- | 1.27 |
| K | 1.000 | --- | 25.40 | --- |

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